Kookrin Char

List of Publications by Year
in descending order

Version: 2024-02-01

164 papers	8,842 citations	41627 51 h-index	49824 91 g-index
166 all docs	166 docs citations	166 times ranked	5185 citing authors

#	Article	IF	Citations
1	Optical Properties of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>La</mml:mi><mml:mi>In</mml:mi><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mn>3</mml:mn></mml:msub><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mn>3</mml:mn></mml:msub></mml:math> Interface Analyzed by Poisson-SchrÃ¶dinger Equation. Physical Review Applied, 2022, 17, .	1.5	7
2	High-Mobility Field-Effect Transistor Using 2-Dimensional Electron Gas at the LaScO₃/BaSnO₃ Interface. ACS Applied Electronic Materials, 2022, 4, 356-366.	2.0	13
3	High- k perovskite gate oxide for modulation beyond 10 ¹⁴ cm ^{â^'2}. Science Advances, 2022, 8, eabm3962.	4.7	6
4	Deep-UV Transparent Conducting Oxide La-Doped SrSnO₃ with a High Figure of Merit. ACS Applied Electronic Materials, 2022, 4, 3623-3631.	2.0	7
5	Fermi level pinning and band bending in Î´-doped BaSnO3. Applied Physics Letters, 2021, 118, 052101.	1.5	2
6	The role of coherent epitaxy in forming a two-dimensional electron gas at LaIn1-xGaxO3/BaSnO3 interfaces. Communications Materials, 2021, 2, .	2.9	5
7	Melt Growth and Physical Properties of Bulk LaInO 3 Single Crystals. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100016.	0.8	9
8	Thin film transistors based on ultra-wide bandgap spinel ZnGa2O4. Applied Physics Letters, 2020, 116, .	1.5	24
9	Remote Doping of the Two-Dimensional-Electron-Gas State at the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>La</mml:mi><mml:mi>In</mml:mi><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mn>3</mml:mn></mml:msub></mml:math> / <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Ba</mml:mi><mml:mi>Sn</mml:mi><mml:mi><mml:ani math	1.5	10
10	Transparent thin film transistors of polycrystalline SnO2â^'x and epitaxial SnO2â^'x. AIP Advances, 2020, 10, .	0.6	9
11	Role of the interface in controlling the epitaxial relationship between orthorhombic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>LaInO</mml:mi><mml:mn>3</mml:mn></mml:msub><m and cubic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BaSnO</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:math Physical Review Materials, 2020, 4	0.9	9
12	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msqrt><mml:mn>2</mml:mn></mml:msqrt><mml:mo>Ã—</ surface reconstruction and electronic structure of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BaSnO</mml:mi><mml:mn>3</mml:mn></mml:msub></m film. Physical Review Materials, 2020, 4, .	0.9	4
13	Structural characterization of the LaInO3/BaSnO3 interface via synchrotron scattering. APL Materials, 2019, 7, .	2.2	8
14	Wide bandgap oxides. APL Materials, 2019, 7, .	2.2	2
15	Interface polarization model for a 2-dimensional electron gas at the BaSnO3/LaInO3 interface. Scientific Reports, 2019, 9, 16202.	1.6	19
16	Identification of F impurities in F-doped ZnO by synchrotron X-ray absorption near edge structures. Journal of Applied Physics, 2018, 123, 161528.	1.1	1
17	LaInO3/BaSnO3 polar interface on MgO substrates. APL Materials, 2018, 6, .	2.2	40
18	Band gap and mobility of epitaxial perovskite BaSn1â^'xHfxO3 thin films. Physical Review Materials, 2018, 2, .	0.9	3

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19	High-k perovskite gate oxide BaHfO3. APL Materials, 2017, 5, .	2.2	28
20	Observation of the Ni₂O₃ phase in a NiO thinâ€film resistive switching system. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700048.	1.2	9
21	Conducting interface states at LaInO3/BaSnO3 polar interface controlled by Fermi level. APL Materials, 2016, 4, .	2.2	36
22	High mobility BaSnO3 films and field effect transistors on non-perovskite MgO substrate. Applied Physics Letters, 2016, 109, .	1.5	66
23	Photoconductivity of transparent perovskite semiconductor BaSnO3 and SrTiO3 epitaxial thin films. Applied Physics Letters, 2016, 108, .	1.5	22
24	Thermally stable pn-junctions based on a single transparent perovskite semiconductor BaSnO3. APL Materials, 2016, 4, .	2.2	28
25	High-mobility BaSnO₃ thin-film transistor with HfO₂ gate insulator. Applied Physics Express, 2016, 9, 011201.	1.1	44
26	Statistical investigation of the length-dependent deviations in the electrical characteristics of molecular electronic junctions fabricated using the direct metal transfer method. Journal of Physics Condensed Matter, 2016, 28, 094003.	0.7	7
27	High mobility field effect transistor of SnOx on glass using HfOx gate oxide. Current Applied Physics, 2016, 16, 300-304.	1.1	11
28	High electron mobility in epitaxial SnO2â^'x in semiconducting regime. APL Materials, 2015, 3, .	2.2	34
29	Oxygen diffusion process in a Ba_{0.96}La_{0.04}SnO₃thin film on SrTiO₃(001) substrate as investigated by time-dependent Hall effect measurements. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1487-1493.	0.8	27
30	All-perovskite transparent high mobility field effect using epitaxial BaSnO3 and LaInO3. APL Materials, 2015, 3, .	2.2	107
31	High mobility field effect transistor based on BaSnO3 with Al2O3 gate oxide. Applied Physics Letters, 2014, 105, .	1.5	90
32	Dopant-site-dependent scattering by dislocations in epitaxial films of perovskite semiconductor BaSnO3. APL Materials, 2014, 2, .	2.2	61
33	Large effects of dislocations on high mobility of epitaxial perovskite Ba_{0.96}La_{0.04}SnO₃ films. Applied Physics Letters, 2013, 102, 252105.	1.5	82
34	Electrical properties of the amorphous interfacial layer between Al electrodes and epitaxial NiO films. Applied Physics Letters, 2012, 100, 172101.	1.5	0
35	Physical properties of transparent perovskite oxides (Ba,La)SnO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>with high electrical mobility at room temperature. Physical Review B, 2012, 86, .	1.1	264
36	High Mobility in a Stable Transparent Perovskite Oxide. Applied Physics Express, 2012, 5, 061102.	1.1	338

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37	High carrier mobility in transparent Ba1âˆ’xLaxSnO3 crystals with a wide band gap. Applied Physics Letters, 2012, 100, .	1.5	170
38	Role of oxygen vacancies formed between top electrodes and epitaxial NiO films in bipolar resistance switching. Current Applied Physics, 2012, 12, 369-372.	1.1	10
39	Effects of tensile stress on the resonant response of Al thin-film and Al-CNT nanolaminate nanomechanical beam resonators. Current Applied Physics, 2011, 11, 746-749.	1.1	6
40	Investigation of Interface Formed between Top Electrodes and Epitaxial NiO Films for Bipolar Resistance Switching. Japanese Journal of Applied Physics, 2010, 49, 031102.	0.8	19
41	Equal-spin triplet<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>p</mml:mi></mml:math>-wave pairing in Nb/Ni proximity effect bilayers. Physical Review B, 2010, 81, .	1.1	5
42	Effect of Cation Substitution on Bipolar Resistance Switching Behavior in Epitaxially Grown NiO Films. Japanese Journal of Applied Physics, 2010, 49, 075801.	0.8	2
43	Effect of F-inclusion in nm-thick MgO tunnel barrier. Current Applied Physics, 2009, 9, 788-791.	1.1	3
44	High-frequency micromechanical resonators from aluminiumâ€“carbon nanotube nanolaminates. Nature Materials, 2008, 7, 459-463.	13.3	46
45	Anomalous Double Peak Structure in Superconductor/Ferromagnet Tunneling Density of States. Physical Review Letters, 2008, 100, 237002.	2.9	35
46	Resistive memory switching in epitaxially grown NiO. Applied Physics Letters, 2007, 91, 202115.	1.5	60
47	Observation of biological samples using a scanning microwave microscope. Ultramicroscopy, 2005, 102, 101-106.	0.8	32
48	Critical thickness of ultrathin ferroelectric BaTiO3 films. Applied Physics Letters, 2005, 86, 102907.	1.5	198
49	Characterization of aluminum oxyfluoride barrier in magnetic tunnel junctions. Journal of Applied Physics, 2004, 96, 2278-2285.	1.1	15
50	Electrical characteristics and interface structure of magnetic tunnel junctions with aluminum oxyfluoride barrier. Applied Physics Letters, 2004, 84, 3334-3336.	1.5	6
51	Electrical characteristics and interface structure of magnetic tunnel junctions with hafnium oxyfluoride barrier. Journal of Applied Physics, 2004, 96, 6393-6397.	1.1	2
52	Nanostructured Metal Surfaces Fabricated by a Nonlithographic Template Method. Langmuir, 2004, 20, 287-290.	1.6	16
53	Narrow passband high-temperature superconducting filters of highly compact sizes for personal communication service applications. IEEE Transactions on Applied Superconductivity, 2003, 13, 17-19.	1.1	15
54	Evolution of Electrical Properties of Magnetic Tunnel Junction through Successive Dielectric Breakdowns. Japanese Journal of Applied Physics, 2003, 42, 1242-1245.	0.8	5

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55	Transport properties of high-angle grain boundaries in Co-dopedYBa2Cu3O7â˜Î´thin films. Physical Review B, 2002, 65, .	1.1	1
56	Performance of high-temperature superconducting band-pass filters with high selectivity for base transceiver applications of digital cellular communication systems. Superconductor Science and Technology, 2002, 15, 1147-1150.	1.8	0
57	Coexistence of metallic and insulating phases in epitaxial CaRuO3 thin films observed by scanning microwave microscopy. Applied Physics Letters, 2002, 80, 1574-1576.	1.5	24
58	Effects of strain on the dielectric properties of tunable dielectric SrTiO3 thin films. Applied Physics Letters, 2001, 79, 254-256.	1.5	90
59	Dielectric Morphology of Twin Domains in LaAlO3Observed by a Scanning Microwave Microscope. Japanese Journal of Applied Physics, 2001, 40, 6510-6513.	0.8	8
60	Anisotropic tuning behavior in epitaxial Ba0.5Sr0.5TiO3 thin films. Applied Physics Letters, 2000, 77, 3084-3086.	1.5	49
61	Electronic transport inBa1â˜xKxBiO3single crystals. Physical Review B, 2000, 61, 14815-14820.	1.1	11
62	Interface chemistry and electrical properties of SrVO3/LaAlO3 heterostructures. Journal of Applied Physics, 2000, 88, 7056-7059.	1.1	10
63	Synthesis and Magnetic Studies of Uniform Iron Nanorods and Nanospheres. Journal of the American Chemical Society, 2000, 122, 8581-8582.	6.6	581
64	Interface-engineered YBCO edge junctions. IEEE Transactions on Applied Superconductivity, 1999, 9, 3358-3361.	1.1	16
65	The effect of microstructure on the electrical properties of YBCO interface-engineered Josephson junctions. Physica C: Superconductivity and Its Applications, 1999, 314, 36-42.	0.6	39
66	Electromigration study of SNS ramp edge Josephson junctions. Applied Superconductivity, 1999, 6, 511-517.	0.5	2
67	Interface-Engineered High-Tc Josephson Junctions. Applied Superconductivity, 1998, 6, 317-323.	0.5	5
68	High-resolution secondary ion mass spectrometry depth profiling of superconducting thin films. Thin Solid Films, 1998, 317, 237-240.	0.8	3
69	Scanning probe microscopy for the imaging and control of ferroelectric oxides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 56, 173-177.	1.7	4
70	Transport across conducting ferromagnetic oxide/metal interfaces. Applied Physics Letters, 1998, 73, 1736-1738.	1.5	36
71	Response to â€˜Comment on â€œProperties of interface-engineered high Tc Josephson junctionsâ€â€‰â€™ [Appl. Phys. Lett. 73, 1745 (1998)]. Applied Physics Letters, 1998, 73, 1747-1747.	1.5	1
72	Ti and Ca substitution in SrRuO3 thin films by sequential deposition process. Applied Physics Letters, 1997, 70, 126-128.	1.5	38

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73	High-Tc superconducting gradiometer with a long baseline asymmetric flux transformer. Applied Physics Letters, 1997, 71, 1712-1714.	1.5	41
74	Properties of interface-engineered high Tc Josephson junctions. Applied Physics Letters, 1997, 71, 2526-2528.	1.5	197
75	Micro-Raman spectroscopy studies of Co doped Y-Ba-Cu-O thin films. IEEE Transactions on Applied Superconductivity, 1997, 7, 3658-3661.	1.1	4
76	High-Tc edge junctions with Y0.8Pr0.2Ba2Cu2.7Co0.3O7â^'Î´ barrier layers near the metalâ€“insulator transition. Applied Physics Letters, 1997, 70, 3152-3154.	1.5	10
77	Ferroelectric field effect in ultrathin SrRuO3 films. Applied Physics Letters, 1997, 70, 206-208.	1.5	104
78	High-T/sub c/ superconductor oversampled delta modulator for analog-to-digital converters. IEEE Transactions on Applied Superconductivity, 1997, 7, 2292-2295.	1.1	5
79	Local, Nonvolatile Electronic Writing of Epitaxial Pb(Zr0.52Ti0.48)O3/SrRuO3 Heterostructures. Science, 1997, 276, 1100-1103.	6.0	256
80	Characterisation of thin film superconducting multilayers and their interfaces using secondary ion mass spectrometry. Journal of Alloys and Compounds, 1997, 251, 355-359.	2.8	4
81	Transmission Electron Microscopy Microstructure Characterization of YBCO/SrRuO₃/YBCO Josephson Junctions. Microscopy and Microanalysis, 1997, 3, 108-120.	0.2	6
82	Supercurrent distribution and flux penetration in high-T c edge Josephson junctions. , 1996, , .		0
83	Transport and magnetic properties of Sr(Ru1â^'xTix)O3 thin films. European Physical Journal D, 1996, 46, 2105-2106.	0.4	4
84	Properties of cobalt-doped YBa2Cu3O7â^'Î´ thin films. Physica C: Superconductivity and Its Applications, 1996, 265, 283-294.	0.6	24
85	Ferroelectric field effect in SrCuO2 and SrRuO3 films. Journal of Low Temperature Physics, 1996, 105, 1517-1522.	0.6	5
86	Bi-epitaxial grain boundaries in YBa₂Cu₃O_{7â^'x} thin films prepared by pulsed laser deposition and pulsed organometallic beam epitaxy: Direct comparison of transport properties and grain boundary structure. Journal of Materials Research, 1996, 11, 2429-2439.	1.2	9
87	Interface structure of a YBa₂Cu₃O_{7â^'x}/N/YBa₂Cu₃O_{7â^'x} superconductor/normal metal/superconductor Josephson junction using YBa₂Cu_{2.79}Co_{0.21}O_{7â^'x} as the normal barrier N. Journal of Materials Research, 1996, 11, 281-287.	1.2	9
88	Pair Tunneling fromc-AxisYBa2Cu3O7â^'xto Pb: Evidence fors-Wave Component from Microwave Induced Steps. Physical Review Letters, 1996, 76, 2161-2164.	2.9	128
89	A multilayer YBa2Cu3Ox Josephson junction process for digital circuit applications. Applied Physics Letters, 1996, 68, 3808-3810.	1.5	63
90	Supercurrent distributions in YBa2Cu3O7â€“YBa2Co0.21Cu2.79O7â€“YBa2Cu3O7 edge Josephson junctions. Applied Physics Letters, 1996, 68, 2279-2281.	1.5	6

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91	Highâ€temperature superconducting Josephson fluxonâ€“antifluxon transistors. Applied Physics Letters, 1996, 69, 3257-3259.	1.5	10
92	Low noise highâ€temperature superconducting bolometers for infrared imaging. Applied Physics Letters, 1996, 69, 2125-2127.	1.5	36
93	Conductanceâ€“voltage characteristics of interfaces between YBa2Cu3O7 and metallic oxides. Applied Physics Letters, 1996, 68, 1009-1011.	1.5	14
94	Interface microstructure and composition of a YBa2Cu3O7â^'x/N/YBa2Cu3O7â^'x SNS edge junction with CaRuO3 as the metallic barrier. Physica C: Superconductivity and Its Applications, 1995, 252, 348-360.	0.6	9
95	Magnetoresistance probe of spatial current variations in highâ€Tc YBa2Cu3O7â€“SrRuO3â€“YBa2Cu3O7 Josephson junctions. Applied Physics Letters, 1995, 67, 1313-1315.	1.5	27
96	Magnetoresistance properties of thin films of the metallic oxide ferromagnetSrRuO3. Physical Review B, 1995, 52, 3459-3465.	1.1	70
97	Electron beam damaged high-T/sub c/ junctions-stability, reproducibility and scaling laws. IEEE Transactions on Applied Superconductivity, 1995, 5, 3410-3413.	1.1	28
98	Fabrication of all thinâ€film YBa2Cu3O7â^'Î´â€‰/Pb Josephson tunnel junctions. Applied Physics Letters, 1995, 66, 105-107.	1.5	54
99	Properties of high-TcJosephson junctions withY0.7Ca0.3Ba2Cu3O7â^'Î´barrier layers. Physical Review B, 1995, 52, 4559-4567.	1.1	42
100	Phonon anomalies at the magnetic phase transition inSrRuO3. Physical Review B, 1995, 51, 12825-12828.	1.1	48
101	Perpendicular magnetic anisotropy and strong magnetoâ€optic properties of SrRuO3 epitaxial films. Applied Physics Letters, 1995, 66, 2427-2429.	1.5	105
102	Proximity effect inYBa2Cu3O7â^'Î´/YBa2(Cu1â^'xCox)3O7â^'Î´/YBa2Cu3O7â^'Î´ junctions: From the clean limit to the dirty limit the clean limit to the dirty limit with pair breaking. Physical Review B, 1995, 51, 8560-8563.	1.1	47
103	Correlation of Vortex Motion in High-TcSuperconductors. Physical Review Letters, 1995, 74, 2796-2799.	2.9	12
104	Voltage-current characteristics and noise properties of SNS junctions. IEEE Transactions on Applied Superconductivity, 1995, 5, 2973-2975.	1.1	7
105	Noise characteristics of YBa2Cu3O7â^'Î´â€‰/CaRuO3/YBa2Cu3O7â^'Î´ Josephson junctions. Applied Physics Letters, 1994, 64, 788-790.	1.5	19
106	Evidence for parallel junctions within high-Tcgrain-boundary junctions. Physical Review B, 1994, 50, 9409-9418.	1.1	36
107	Origin of nonuniform properties of YBa2Cu3O7â^'x/CaRuO3/YBa2Cu3O7â^'xJosephson edge junctions. Applied Physics Letters, 1994, 64, 1292-1294.	1.5	38
108	High-temperature superconducting shift registers operating at up to 100 GHz. IEEE Journal of Solid-State Circuits, 1994, 29, 56-62.	3.5	7

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109	Properties of YBa2Cu3O7â^'x/YBa2Cu2.79Co0.21O7â^'x/YBa2Cu3O7â^'xedge junctions. Applied Physics Letters, 1994, 65, 904-906.	1.5	66
110	<title>High-tempreature superconductor flux-flow devices and applications</title>. , 1994, 2156, 141.		0
111	Use of 2-dimensional arrays to determine the uniformity of Josephson junctions. IEEE Transactions on Applied Superconductivity, 1993, 3, 3095-3101.	1.1	4
112	Study of interface resistances in epitaxial YBa2Cu3O7â^'x/barrier/YBa2Cu3O7â^'xjunctions. Applied Physics Letters, 1993, 63, 2420-2422.	1.5	138
113	Sensitive bolometers using highâ€Tcsuperconducting thermometers for wavelengths 20â€“300 Î¼m. Journal of Applied Physics, 1993, 74, 4251-4253.	1.1	20
114	Multichip module using multilayer YBa2Cu3O7â^'Î'interconnects. Applied Physics Letters, 1993, 62, 1435-1437.	1.5	39
115	Design of high-T/sub c/ superconducting bolometers for a far infrared imaging array. IEEE Transactions on Applied Superconductivity, 1993, 3, 2115-2119.	1.1	8
116	Halfâ€integral constant voltage steps in highâ€Tcgrain boundary junctions. Applied Physics Letters, 1993, 62, 3357-3359.	1.5	62
117	High performance dc SQUID magnetometers with single layer YBa2Cu3O7â^'xflux transformers. Applied Physics Letters, 1993, 63, 3630-3632.	1.5	67
118	Josephson coupling of YBa2Cu3O7â^'xthrough a ferromagnetic barrier SrRuO3. Applied Physics Letters, 1993, 63, 1005-1007.	1.5	106
119	Noise properties of biepitaxial HTS junctions. IEEE Transactions on Applied Superconductivity, 1993, 3, 2319-2320.	1.1	17
120	Superconducting Josephson arrays as tunable microwave sources operating at 77 K. Applied Physics Letters, 1993, 63, 1681-1683.	1.5	35
121	HighTcsuperconductorâ€normalâ€superconductor Josephson junctions using CaRuO3as the metallic barrier. Applied Physics Letters, 1993, 62, 196-198.	1.5	133
122	Flicker (1/f) noise in biepitaxial grain boundary junctions of YBa2Cu3O7â^'x. Applied Physics Letters, 1992, 60, 1899-1901.	1.5	85
123	Largeâ€area YBa2Cu3O7â^'Î'thin films on sapphire for microwave applications. Applied Physics Letters, 1992, 61, 1727-1729.	1.5	104
124	Microstructure of biepitaxial grain boundary junctions in YBa2Cu3O7. Applied Physics Letters, 1992, 60, 1010-1012.	1.5	33
125	Feasibility of infrared imaging arrays using highâ€Tcsuperconducting bolometers. Journal of Applied Physics, 1992, 71, 2491-2498.	1.1	51
126	Multilayer superconducting devices made using biepitaxial grain boundary Josephson junctions in YBa 2 Cu 3 O 7. , 1992, , .		0

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127	Freeâ€standing microstructures of YBa2Cu3O7â^'Î´: A highâ€temperature superconducting air bridge. Applied Physics Letters, 1992, 61, 2706-2708.	1.5	16
128	A phase sensitive technique for the study of noise properties of HTS junctions. Cryogenics, 1992, 32, 715-718.	0.9	5
129	Fabrication of an infrared bolometer with a high T/sub c/ superconducting thermometer. IEEE Transactions on Magnetics, 1991, 27, 3077-3080.	1.2	45
130	Biâ€epitaxial grain boundary junctions in YBa2Cu3O7. Applied Physics Letters, 1991, 59, 733-735.	1.5	299
131	Thin-film YBCO magnetometer. Nature, 1991, 352, 482-483.	13.7	18
132	Monolithic 77 K dc SQUID magnetometer. Applied Physics Letters, 1991, 59, 3051-3053.	1.5	151
133	Double gun off-axis sputtering of large area YBa/sub 2/Cu/sub 3/O/sub 7- delta / superconducting films for microwave applications. IEEE Transactions on Magnetics, 1991, 27, 1276-1279.	1.2	57
134	Enhancement of optical reflectivity of highTcsuperconducting films by ion milling. Applied Physics Letters, 1991, 58, 2558-2560.	1.5	0
135	Thermal boundary resistance for YBa2Cu3O7â^'Î´films. Applied Physics Letters, 1991, 59, 2034-2036.	1.5	127
136	Extension of the biâ€epitaxial Josephson junction process to various substrates. Applied Physics Letters, 1991, 59, 2177-2179.	1.5	120
137	Sensitive YBa2Cu3O7â^'xthinâ€film magnetometer. Applied Physics Letters, 1991, 59, 988-990.	1.5	77
138	Observation of two inâ€plane epitaxial states in YBa2Cu3O7â^'Î´films on yttriaâ€stabilized ZrO2. Applied Physics Letters, 1991, 58, 2168-2170.	1.5	97
139	Flux focusing effects in planar thinâ€film grainâ€boundary Josephson junctions. Applied Physics Letters, 1991, 59, 3482-3484.	1.5	221
140	Microwave surface resistance of epitaxial YBa2Cu3O7thin films on sapphire. Applied Physics Letters, 1990, 57, 409-411.	1.5	108
141	Variation of Cu-O charge-transfer energies inYBa2Cu3O7â^'xthin films studied by photoemission spectroscopy. Physical Review B, 1990, 42, 8044-8048.	1.1	27
142	YBa2Cu3O7â^'Î´superconducting films with low microwave surface resistance over large areas. Applied Physics Letters, 1990, 57, 520-522.	1.5	99
143	Properties of epitaxial YBa2Cu3O7thin films on Al2O3â€‰{1Ì„012}. Applied Physics Letters, 1990, 56, 785-787.	1.5	79
144	Microstructural interaction of Y₂Ba₄Cu₈O₁₆ stacking faults within YBa₂Cu₃O_{7â^'x}. Journal of Materials Research, 1990, 5, 2049-2055.	1.2	40

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145	<title>Fabrication of a high Tc superconducting bolometer</title>. , 1990, 1292, 137.		3
146	Power-law temperature dependence of the electrodynamic properties in orientedYBa2Cu3O7âˆ'Î´andY2Ba4Cu8O16âˆ'Î´films. Physical Review B, 1989, 39, 785-788.	1.1	38
147	Orthorhombic distortion and cation ordering inY2Ba4Cu8O16andEr2Ba4Cu8O16high-Tcthin films. Physical Review B, 1989, 39, 11648-11652.	1.1	7
148	Resonance effects in Raman scattering in YBa2Cu3O7. Journal of Applied Physics, 1989, 66, 977-979.	1.1	25
149	Magnetic flux motion and its influence on transport properties of the high Tc oxide superconductors. Applied Physics Letters, 1989, 54, 663-665.	1.5	88
150	Growth and properties of sputtered high-T/sub c/ oxide thin films. IEEE Transactions on Magnetics, 1989, 25, 2422-2425.	1.2	24
151	Microstructural characterization of YBa/sub 2/Cu/sub 3/O/sub 7- delta / thin films on SrTiO/sub 3/ using four-axis X-ray diffraction. IEEE Transactions on Magnetics, 1989, 25, 2245-2249.	1.2	13
152	Measurements on thin-film high-T_c superconductors. IBM Journal of Research and Development, 1989, 33, 252-261.	3.2	13
153	Analogy between Y2Ba4Cu8O16âˆ'x and Bi4Ca2Sr4Cu4O16+x. Physica C: Superconductivity and Its Applications, 1988, 152, 475-478.	0.6	19
154	Upper critical field, fluctuation conductivity, and dimensionality ofYBa2Cu3O7âˆ'x. Physical Review B, 1988, 37, 7861-7864.	1.1	411
155	Millimeter-wave surface resistance measurements in highly orientedYBa2Cu3O7âˆ'Î´thin films. Physical Review B, 1988, 37, 9726-9729.	1.1	89
156	Optical anisotropy ofYBa2Cu3O7âˆ'x. Physical Review B, 1988, 38, 5077-5080.	1.1	72
157	Properties of Y-Ba-Cu-O thin films with ordered defect structure:Y2Ba4Cu8O20âˆ'x. Physical Review B, 1988, 38, 834-837.	1.1	145
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